

2SC2603 is NPN silicon planar transistor designed for low power general purpose amplifiers.

TO-92B



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	50V
Collector-Emitter Voltage	VCEO	50V
Emitter-Base Voltage	VEBO	6V
Collector Current	IC	200mA
Total Power Dissipation	Ptot	300mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ECB

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BVCEO	50		V	IC=100μA IB=0
Collector Cutoff Current	ICBO		100	nA	VCB=50V IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=6V IC=0
D.C. Current Gain	HFE	90	800		IC=1mA VCE=6V
		90	180		
		150	300		
		250	500		
		400	800		
		50			IC=100μA VCE=6V
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=100mA IB=10mA*
Current Gain Bandwidth Product	fT	200	TYP	MHz	IC=10mA VCE=6V
Output Capacitance	Cob	2.5	TYP	pF	VCB=6V f=1MHz
Noise Figure	NF		15	dB	IC=0.1mA VCE=6V f=1kHz RG=2kΩ

* Pulse Test : Pulse Width <300us, duty cycle <2%.



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